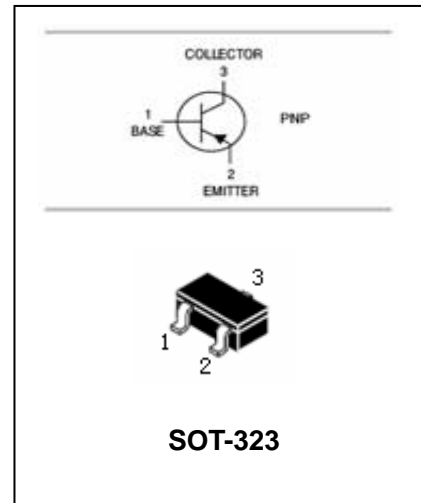


PNP Silicon Epitaxial Planar Transistor

MMST2907A

FEATURES

- Power dissipation.($P_C=200\text{mW}$)
- Epitaxial planar die construction.
- Complementary NPN type MMST2222A.



APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMST2907A	K3F	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-600	mA
P_C	Collector Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	625	$^\circ\text{C}/\text{W}$
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

PNP Silicon Epitaxial Planar Transistor

MMST2907A

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$		-10	nA
Collector cut-off current	I_{CEX}	$V_{CE}=-30V, V_{EB(OFF)}=-0.5V$		-50	nA
Base cut-off current	I_{BL}	$V_{CE}=-30V, V_{EB(OFF)}=-0.5V$		-50	nA
DC current gain	h_{FE}	$V_{CE}=-10V, I_C=-0.1mA$	75		
		$V_{CE}=-10V, I_C=-1.0mA$	100		
		$V_{CE}=-10V, I_C=-10mA$	100		
		$V_{CE}=-10V, I_C=-150mA$	100	300	
		$V_{CE}=-10V, I_C=-500mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150mA, I_B=-15mA$ $I_C=-500mA, I_B=-50mA$		-0.4 -1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150mA, I_B=-15mA$ $I_C=-500mA, I_B=-50mA$		-1.3 -2.6	V
Transition frequency	f_T	$V_{CE}=-20V, I_C=-50mA$ $f=100MHz$	200		MHz
Collector output capacitance	C_{obo}	$V_{CB}=-10V, I_E=0, f=1MHz$		8	pF
Collector input capacitance	C_{ibo}	$V_{EB}=-2.0V, I_C=0, f=1MHz$		30	pF
Turn-on time	t_{on}	$V_{CC}=-30V, I_C=-150mA,$ $I_{B1}=-15mA$		45	nS
Delay time	t_d			10	nS
Rise time	t_r			40	nS
Turn-off time	t_{off}	$V_{CC}=-6.0V, I_C=-150mA,$ $I_{B1}=I_{B2}=-15mA$		100	nS
Storage time	t_s			80	nS
Fall time	t_f			30	nS

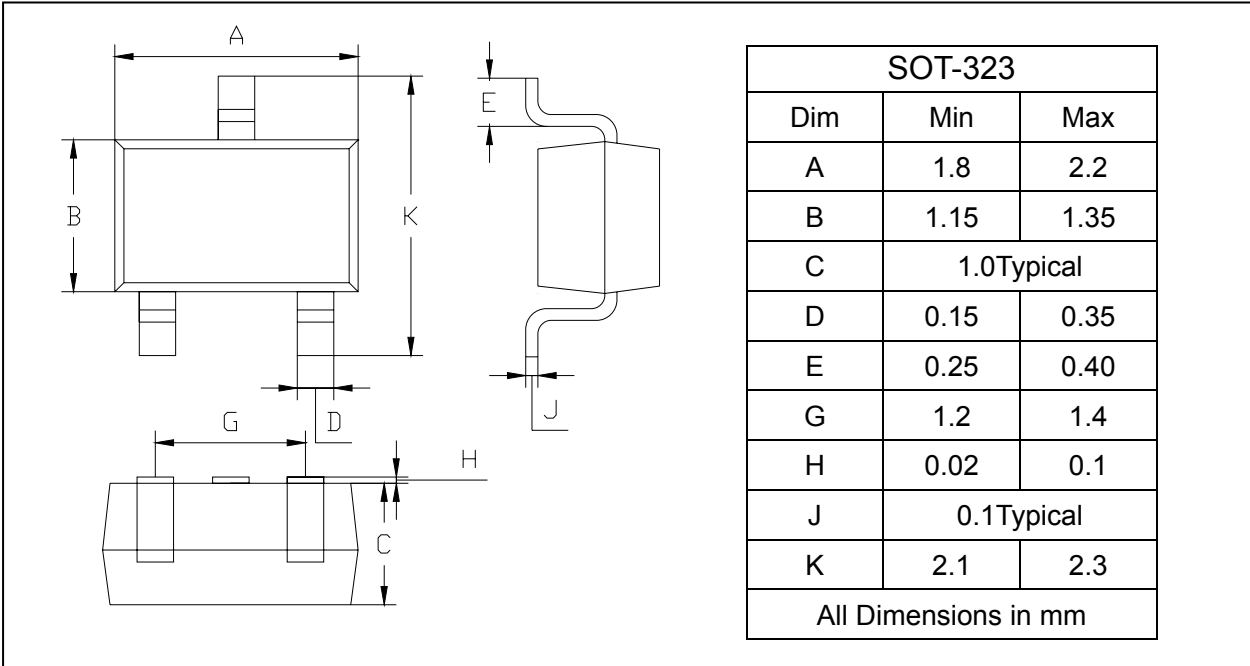
PNP Silicon Epitaxial Planar Transistor

MMST2907A

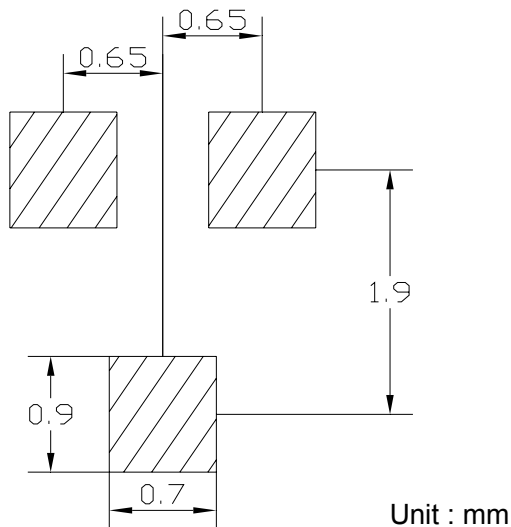
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMST2907A	SOT-323	3000/Tape&Reel

www.s-manuals.com